

Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.022 at $V_{GS} = 10$ V	10
	0.030 at $V_{GS} = 4.5$ V	8.5

SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.50 V at 1.0 A	3.0

FEATURES

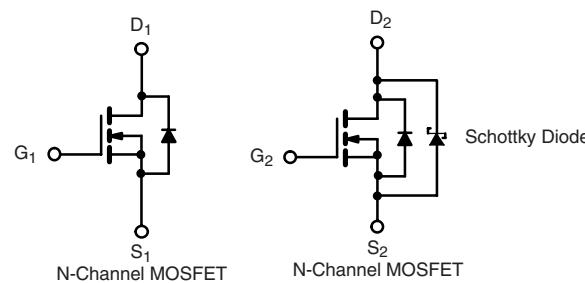
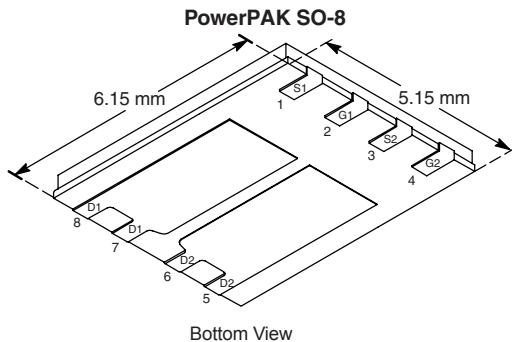
- Halogen-free According to IEC 61249-2-21 Available
- LITTLE FOOT® Plus Schottky
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- 100 % R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Bus and Logic DC-DC



Ordering Information: Si7842DP-T1-E3 (Lead (Pb)-free)
Si7842DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted						
Parameter	Symbol	10 s		Steady State		Unit
Drain-Source Voltage	V_{DS}	30		± 20		V
Gate-Source Voltage	V_{GS}					
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	10		6.3		A
$T_A = 70$ °C		6.0		5.0		
Pulsed Drain Current	I_{DM}	30				A
Continuous Source Current (Diode Conduction) ^a	I_S	2.9		1.1		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C		3.5		W
$T_A = 70$ °C		2.2		0.9		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150				°C
Soldering Recommendations (Peak Temperature) ^{b,c}		260				

THERMAL RESISTANCE RATINGS

Parameter	Symbol	MOSFET		Schottky		Unit
		Typical	Maximum	Typical	Maximum	
Maximum Junction-to-Ambient ^a	R_{thJA}	26	35	26	35	°C/W
Steady State		60	85	60	85	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	3.9	5.5	3.9	5.5

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition		Min.	Typ. ^b	Max.	Unit
Static							
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		0.8		2.4	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$				± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$	Ch-1		1		μA
			Ch-2		100		
		$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 85^\circ\text{C}$	Ch-1		15		
			Ch-2		2000		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} = 5 \text{ V}$, $V_{GS} = 10 \text{ V}$		20			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 7.5 \text{ A}$			0.018	0.022	Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 6.5 \text{ A}$			0.024	0.030	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 7.5 \text{ A}$			22		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1 \text{ A}$, $V_{GS} = 0 \text{ V}$	Ch-1		0.8	1.2	V
			Ch-2		0.47	0.5	
Dynamic^b							
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 7.5 \text{ A}$			13	20	nC
Gate-Source Charge	Q_{gs}				2		
Gate-Drain Charge	Q_{gd}				2.7		
Gate Resistance	R_g			0.5	1.2	3.2	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}$, $R_L = 15 \Omega$ $I_D \geq 1 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 6 \Omega$			8	16	ns
Rise Time	t_r				10	20	
Turn-Off Delay Time	$t_{d(\text{off})}$				21	40	
Fall Time	t_f				10	20	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = 1.7 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$	Ch-1	40	80	
				Ch-2	32	70	

Notes:

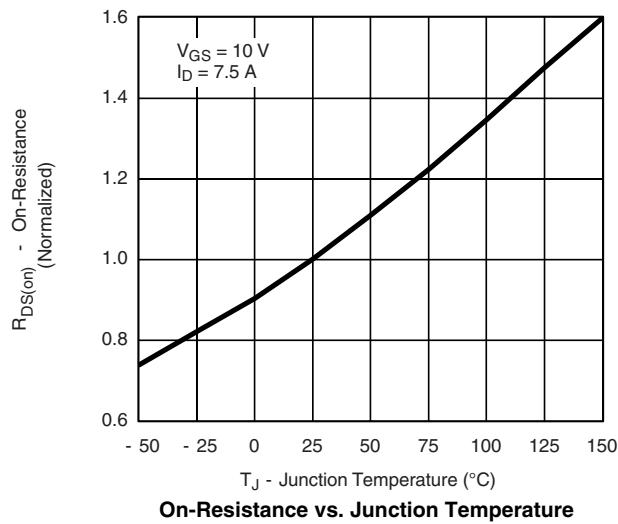
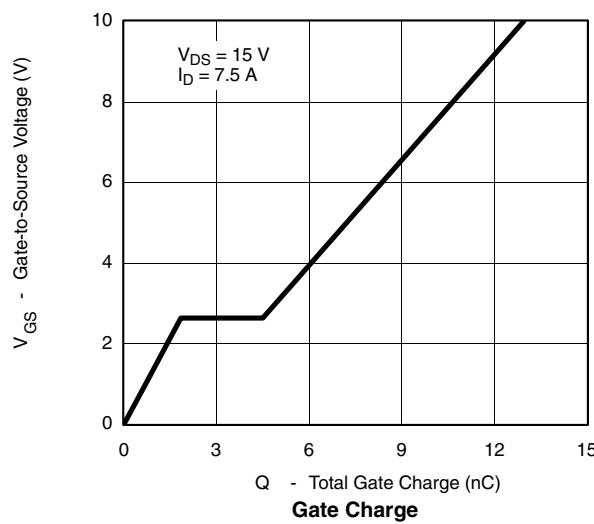
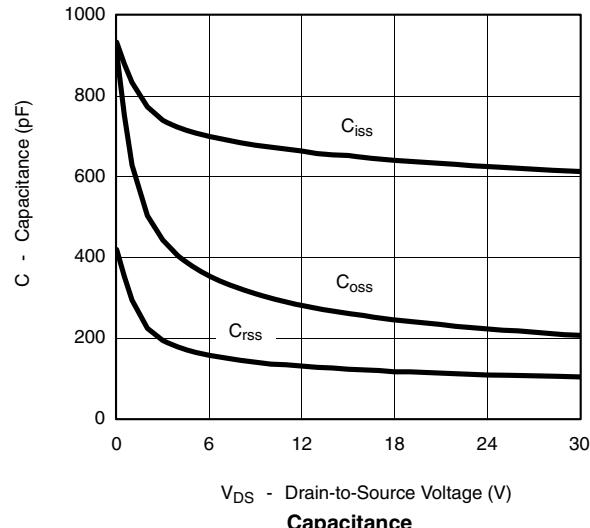
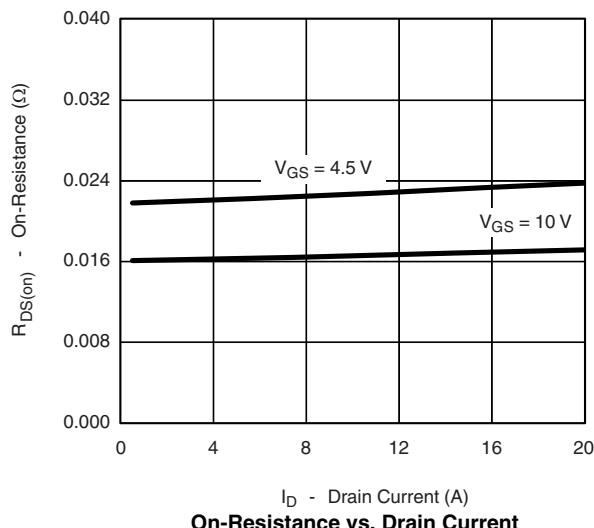
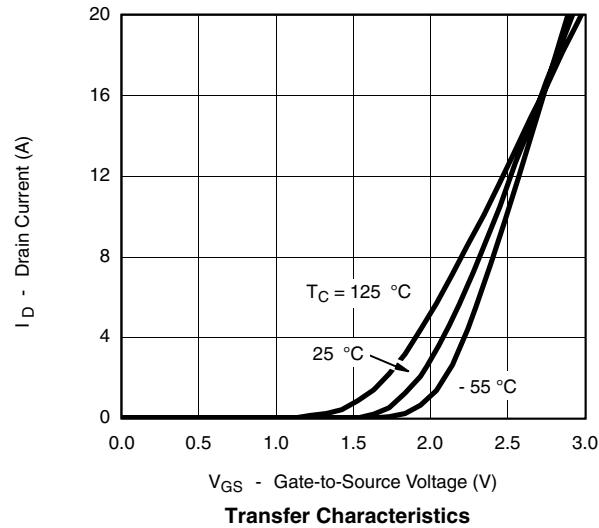
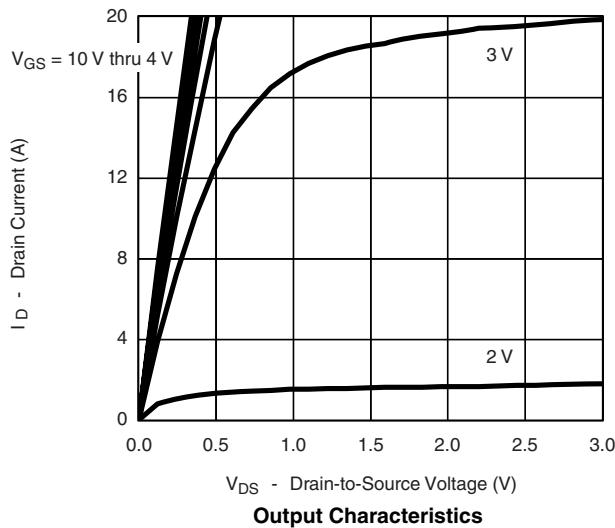
a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

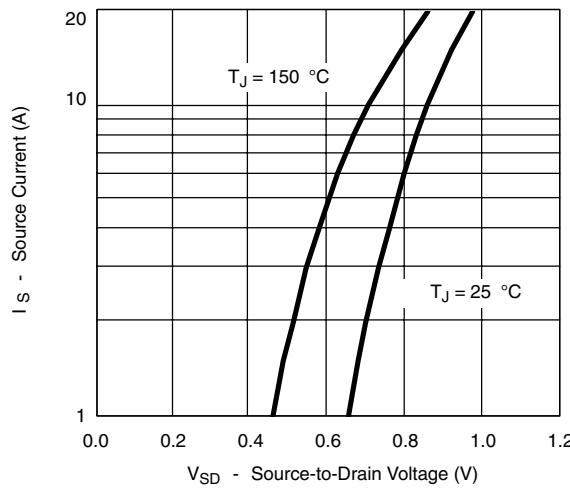
b. Guaranteed by design, not subject to production testing.

SCHOTTKY SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

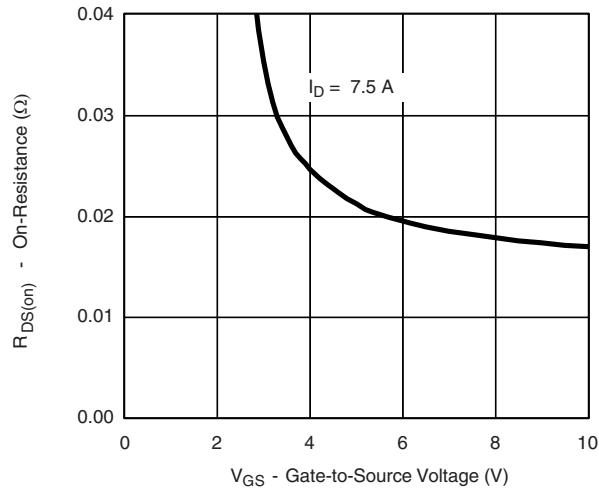
Parameter	Symbol	Test Condition		Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1.0 \text{ A}$			0.47	0.50	V
		$I_F = 1.0 \text{ A}$, $T_J = 125^\circ\text{C}$			0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_r = 30 \text{ V}$			0.004	0.100	mA
		$V_r = 30 \text{ V}$, $T_J = 100^\circ\text{C}$			0.7	10	
		$V_r = -30 \text{ V}$, $T_J = 125^\circ\text{C}$			3.0	20	
Junction Capacitance	C_T	$V_r = 10 \text{ V}$			50		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

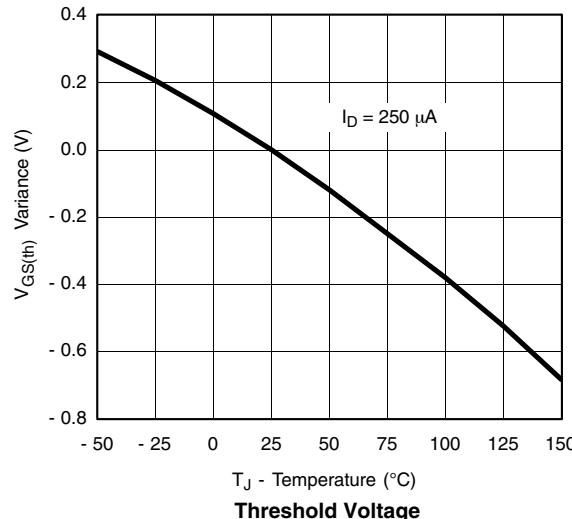
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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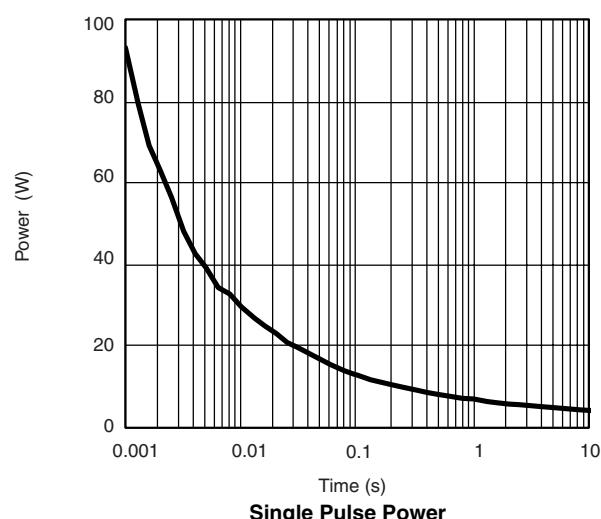
Source-Drain Diode Forward Voltage



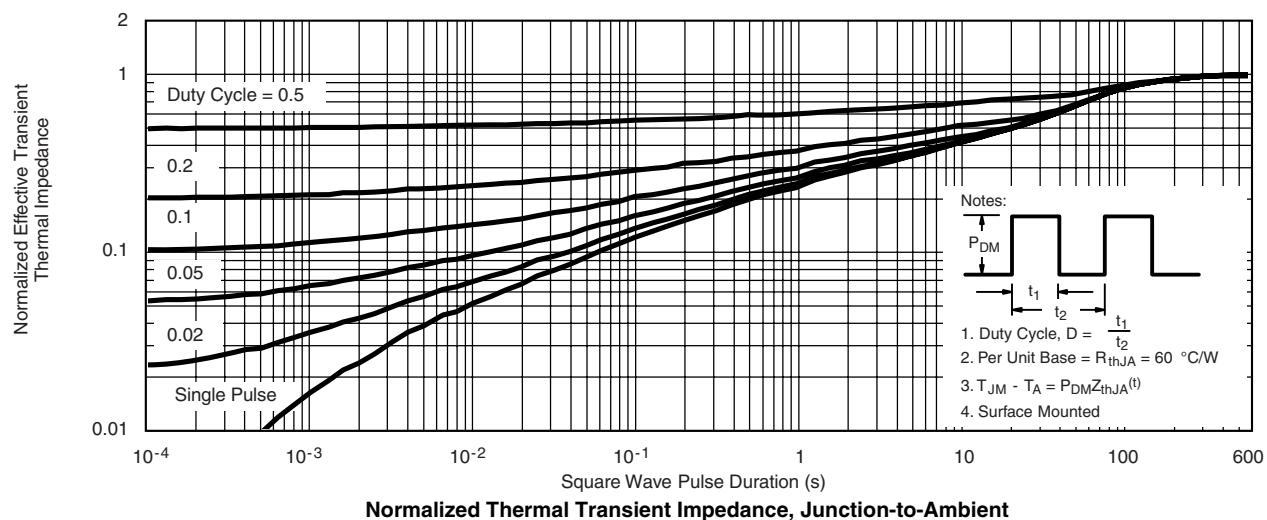
On-Resistance vs. Gate-to-Source Voltage



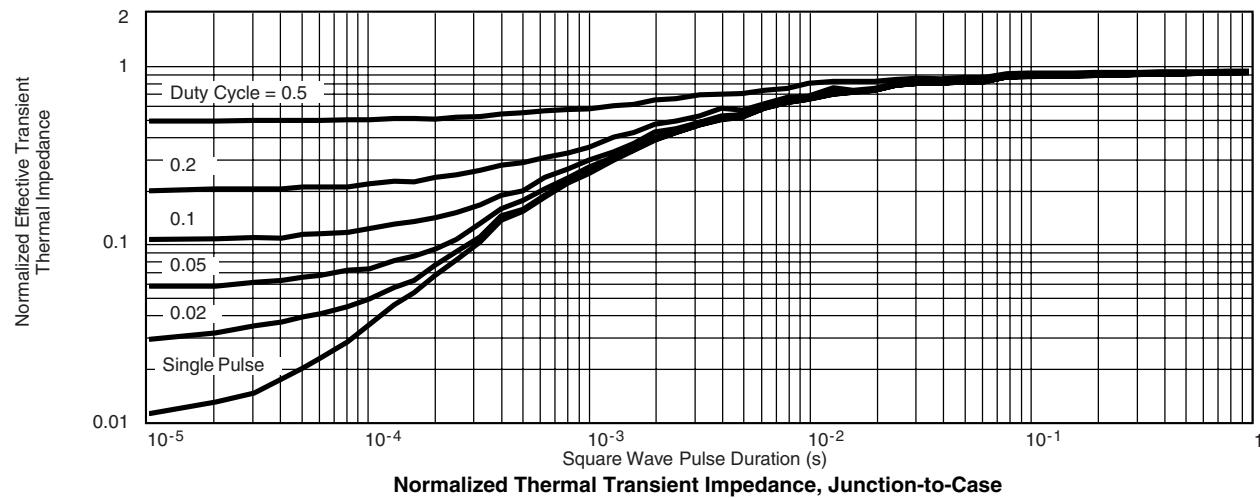
Threshold Voltage



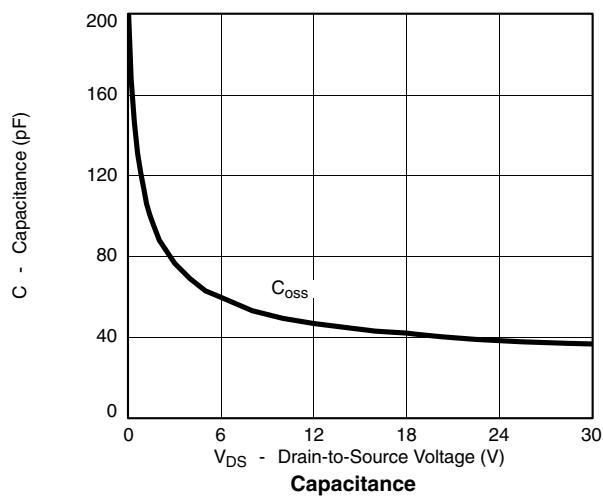
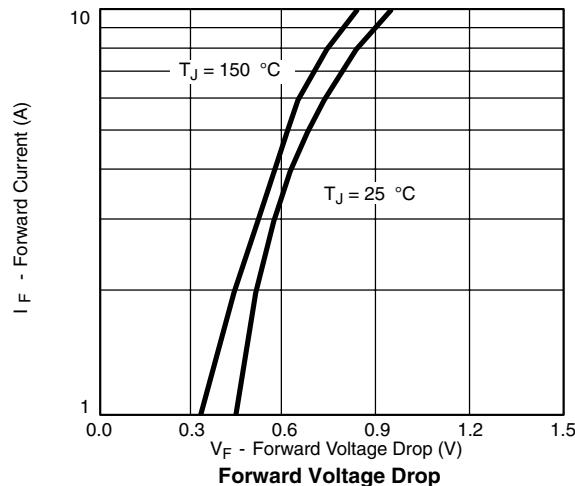
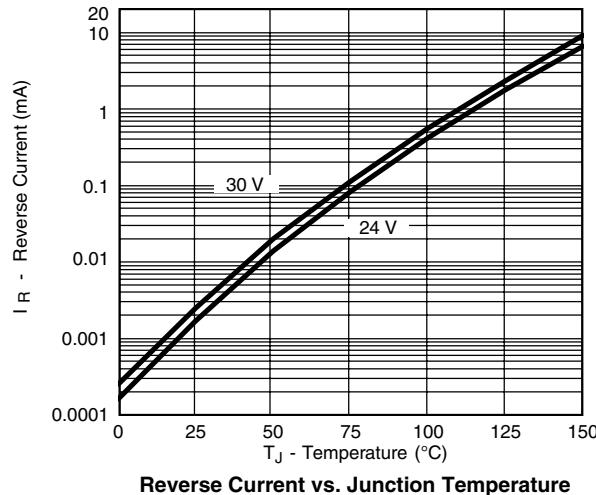
Single Pulse Power



MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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